

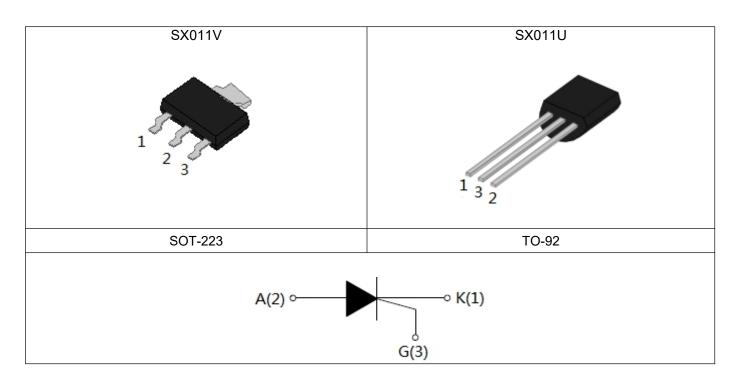




# **SX011 Series Sensitive gate SCRs**

## **Description**

The SX011 SCR series provide high dv/dt rate with strong resistance to electromagnetic interface. They are especially recommended for use on residual current circuit breaker, straight hair, igniter etc.



#### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Storage junction temperature range	TJ	-	-40 to +110	°C
Operating junction temperature range	T <sub>stg</sub>	-	-40 to +150	°C
Repetitive peak off-state voltage	$V_{DRM}$	-	800	V
Repetitive peak reverse voltage	$V_{RRM}$	-	800	V
RMS on-state current		TO-92(T <sub>C</sub> =65°C)	_	_
	I(TRMS)	SOT-223(T <sub>C</sub> =75°C)	1	A
Non repetitive surge peak on-state current(tp=10ms)	I <sub>TSM</sub>	-	12	Α
I2t value for fusing (tp=10ms)	l²t	-	0.72	A <sup>2</sup> s
Critical rate of rise of on-state current	dl/dt	-	50	A/us
Peak gate current (tp=20 μ s, Tj=110℃)	I <sub>GM</sub>	-	0.3	Α
Peak gate power (tp=20 μ s, Tj=110℃)	P <sub>GM</sub>	-	0.5	W
Average gate power dissipation(Tj=110℃)	P <sub>G(AV)</sub>	-	0.1	W

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## **Electrical Characteristics**(Tj=25℃ unless otherwise specified)

Symbol	Condition	Min.	Тур.	Max.	Units
I <sub>GT</sub>	V =43V B =33O	-	40	200	μA
V <sub>GT</sub>	- V <sub>D</sub> =12V R <sub>L</sub> =33Ω	-	0.6	0.8	V
$V_{GD}$	$V_D = V_{DRM} T_j = 110 ^{\circ}C$	0.2	-	-	V
lμ	I <sub>G</sub> =1.2 I <sub>GT</sub>	-	-	5	mA
l <sub>H</sub>	I <sub>T</sub> =0.05A	-	-	4	mA
dV/dt	$V_D=2/3V_{DRM} T_j=110^{\circ}C R_{GK}=1K\Omega$	100	200	-	V/µs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

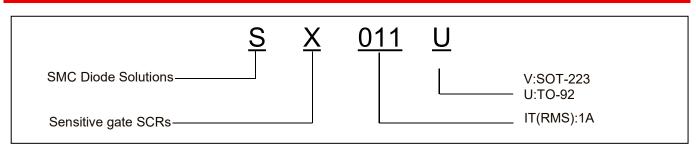
## **Static Characteristics**

Symbol	Symbol Condition		Units
$V_{TM}$	I <sub>T</sub> =2A tp=380μs,Tj=25℃	1.7	V
I <sub>DRM</sub>	V <sub>D</sub> =V <sub>DRM</sub> V <sub>R</sub> =V <sub>RRM</sub> , Tj=25°C	5	uA
I <sub>RRM</sub>	$V_D=V_{DRM} V_R=V_{RRM}$ , $T_j=110^{\circ}C$	100	uA

## **Thermal Resistances**

Symbol	Condition		Value	Units
Rth(j-c)	Junction to case	TO-92	70	°∩ ΛΛ/
		SOT-223	25	°C/W

## **Ordering Information**



Device	Package	Shipping
SX011V	SOT-223	4000pcs/ reel
SX011VTR	SOT-223	4000pcs/ reel
SX011U	TO-92	1000pcs/ bag

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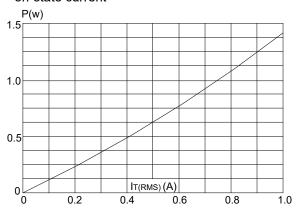




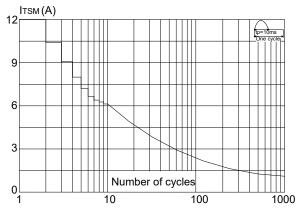


## **Ratings and Characteristics Curves**

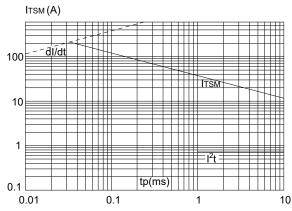
**FIG.1:** Maximum power dissipation versus RMS on-state current



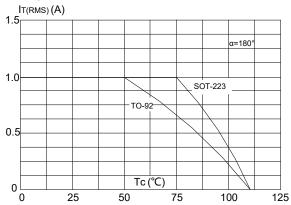
**FIG.3:** Surge peak on-state current versus number of cycles



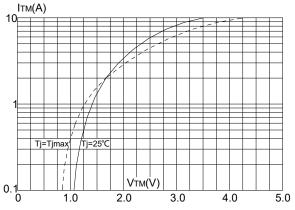
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<10ms (dl/dt  $\leq$  50A/ $\mu$ s)



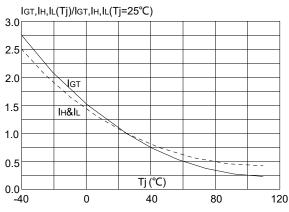
**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics (maximum values)



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature



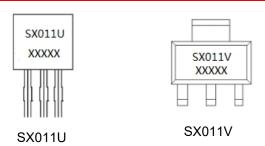
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## **Marking Diagram**

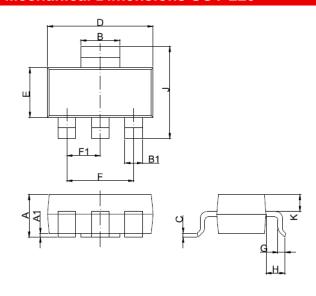


Where XXXXX is YYWWL

S = SMC

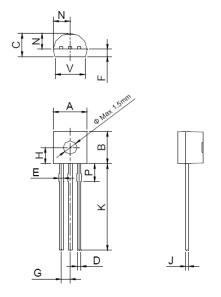
X = Sensitive gate SCRs
011 = Forward Current (1A)
V/U = Package type
YY = Year
WW = Week
L = Lot Number

#### **Mechanical Dimensions SOT-223**



SYMBO	Millimeters			Inches		
L	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	1.5	1.6	1.8	0.059	0.063	0.071
A1	0.01	0.06	0.10	0.001	0.002	0.004
В	2.9	3.0	3.1	0.114	0.118	0.122
B1	0.6	0.7	0.8	0.024	0.028	0.031
С	0.22	0.26	0.32	0.009	0.010	0.013
D	6.3	6.5	6.7	0.248	0.256	0.264
Е	3.3	3.5	3.7	0.130	0.138	0.146
F		4.6			0.181	
F1		2.3			0.091	
G	0.7	0.9	1.1	0.028	0.035	0.043
Н	1.50	1.5	2.0	0.059	0.069	0.079
J	6.7	7.0	7.3	0.264	0.276	0.287
K	0.8	0.9	1.0	0.031	0.035	0.039

#### **Mechanical Dimensions TO-92**



SYMBO	Millimeters			Inches		
L	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	4.45	-	5.20	0.175	-	0.205
В	4.32	-	5.33	0.170	-	0.210
С	3.18	-	4.19	0.125	-	0.165
D	0.407	-	0.533	0.016	-	0.021
E	0.60	-	0.80	0.024	-	0.031
F	-	1.1	-	-	0.043	-
G	-	1.27	-	-	0.050	-
Н	-	2.30	-	-	0.091	-
J	0.36	-	0.50	0.014	-	0.020
K	12.70	-	15.0	0.500	-	0.591
N	2.04	-	2.66	0.080	-	0.105
Р	1.86	-	2.06	0.073	-	0.081
V	-	-	4.3	-	-	0.169

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